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## Patent Abstracts of Japan

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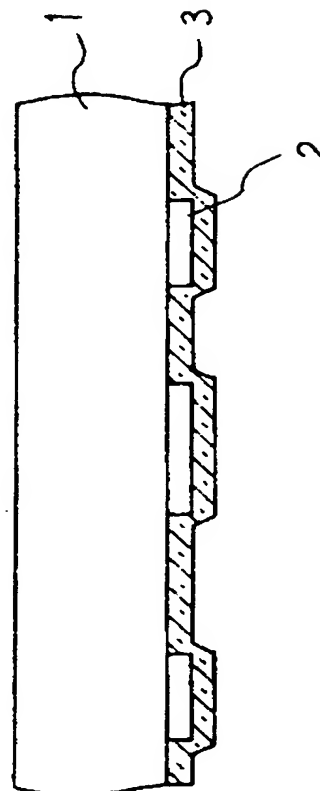
APPLICATION DATE : 21-08-81  
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APPLICANT : NEC CORP;

INVENTOR : TSUDA HIROSHI;

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TITLE : MASK FOR EXPOSURE



ABSTRACT : PURPOSE: To prevent a mask pattern from damage, by covering a surface on which a pattern is formed with a silicon oxide film or a silicon nitride film in relation to the structure of a mask for exposure used in the manufacturing process etc. of a semiconductor element.

CONSTITUTION: A silicon oxide film 3 is stuck for coating the surface by e.g. a CVD growing method or a sputtering method on a chromium oxide layer 2 which is subjected to a patterning on a glass or quartz glass substrate 1. As a glass mask coated with this silicon oxide film 3 durable to an inorg. washing treatment, almost all the org. substance which are stuck on can be removed by washing, and further when the mask is brought into contact with a photoresist of the semiconductor substrate, the chromium oxide layer is not deformed and also not damaged.

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